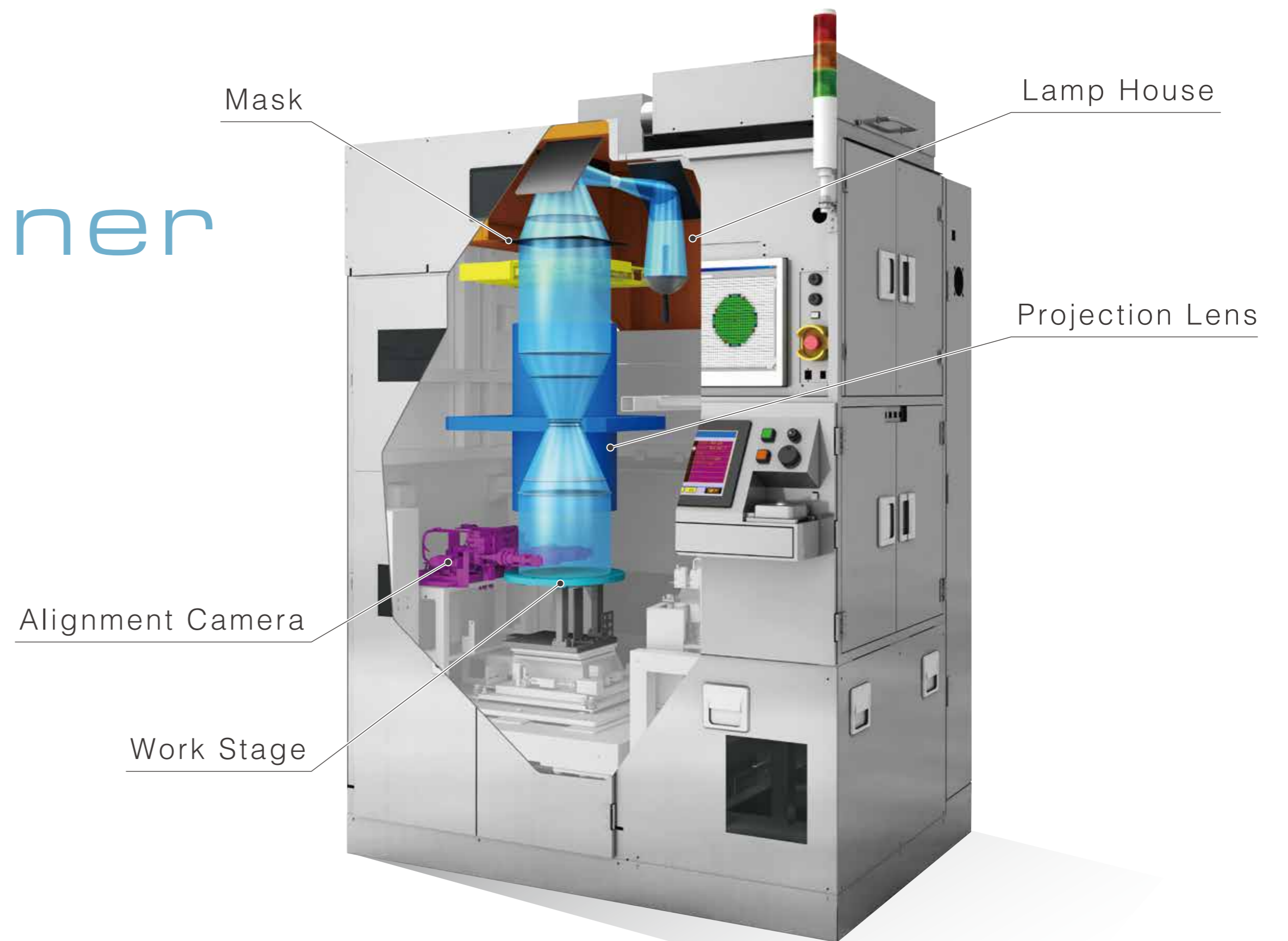


# USHIO

## Full-Field Projection Aligner UX-4

Resolution	2 $\mu$ m L/S~
Overlay	Top Side : $\pm 1\mu$ m, Back Side : $\pm 1.5\mu$ m
Throughput	120wph
Wafer Size	$\Phi 100$ mm / 150mm / 200mm / 300mm Si, Sapphire, GaN, GaAs, SiC, Glass
Wafer Transfer	Cassette to Cassette Automatic



### Advantage of Full-Field Projection Lithography

	UX-4(Full-Field Projection)	Proximity/Contact Aligner
Mask Damage Free	<input checked="" type="checkbox"/> No mask-wafer contact throughout the process.	<input checked="" type="checkbox"/> Damaged
High Productivity	<input checked="" type="checkbox"/> Full-Field Projection > Proximity/Contact Aligner	<input checked="" type="checkbox"/> Exposure → Alignment → Exposure
3D Lithography	<input checked="" type="checkbox"/> Large Depth of Focus. High resolution on both top and bottom of step.	<input checked="" type="checkbox"/> Damaged
Thick Resist Process	<input checked="" type="checkbox"/> No mask-wafer sticking problem with thick-sticky resist.	<input checked="" type="checkbox"/> Stuck

#### Flexibility on wafer format

Legend: Alignment Mark (red), Exposure area (yellow), Wafer (grey), Wafer Stage (dashed blue line).

- TAIKO:60 $\mu$ mt
- SOI:50 $\mu$ mt+625 $\mu$ m
- Wafer with through hall:850 $\mu$ m
- Thick Si Water:1000 $\mu$ m

#### Mask Compatibility

OK

Use your own contact aligner mask. No special mask needed.